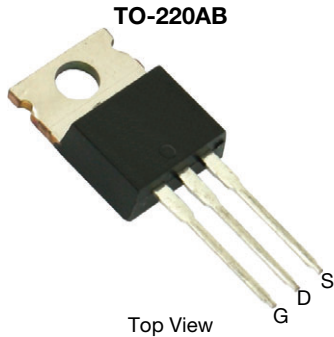


## N-Channel 80 V (D-S) MOSFET



PRODUCT SUMMARY	
$V_{DS}$ (V)	80
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10$ V	0.0024
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 7.5$ V	0.0028
$Q_g$ typ. (nC)	151.2
$I_D$ (A)	150 <sup>d</sup>
Configuration	Single

### FEATURES

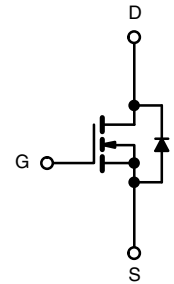
- TrenchFET® power MOSFET
- Maximum 175 °C junction temperature
- Very low  $Q_{gd}$  reduces power loss from passing through  $V_{plateau}$
- 100 %  $R_g$  and UIS tested
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
FREE

### APPLICATIONS

- Power supply  
- Secondary synchronous rectification
- DC/DC converter
- Power tools
- Motor drive switch
- DC/AC inverter
- Battery management
- OR-ing / e-fuse



N-Channel MOSFET

ORDERING INFORMATION	
Package	TO-220
Lead (Pb)-free and halogen-free	SUP60020E-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	80	V
Gate-source voltage	$V_{GS}$	$\pm 20$	
Continuous drain current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	150 <sup>d</sup>
		$T_C = 70$ °C	150 <sup>d</sup>
Pulsed drain current ( $t = 100$ $\mu$ s)	$I_{DM}$	500	A
Avalanche current	$I_{AS}$	60	
Single avalanche energy <sup>a</sup>	$E_{AS}$	180	mJ
Maximum power dissipation <sup>a</sup>	$P_D$	$T_C = 25$ °C	375 <sup>b</sup>
		$T_C = 125$ °C	125 <sup>b</sup>
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +175	°C

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-ambient (PCB mount) <sup>c</sup>	$R_{thJA}$	40	°C/W
Junction-to-case (drain)	$R_{thJC}$	0.4	

#### Notes

- Duty cycle  $\leq 1$  %
- See SOA curve for voltage derating
- When mounted on 1" square PCB (FR4 material)
- Package limited



<b>SPECIFICATIONS</b> ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	80	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	-	4	
Gate-body leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	-	-	$\pm 250$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	$\mu\text{A}$
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	150	
		$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	5	mA
On-state drain current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	120	-	-	A
Drain-source on-state resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30\text{ A}$	-	0.00200	0.00240	$\Omega$
		$V_{GS} = 7.5\text{ V}, I_D = 20\text{ A}$	-	0.00215	0.00280	
Forward transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 30\text{ A}$	-	115	-	S
<b>Dynamic <sup>b</sup></b>						
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 40\text{ V}, f = 1\text{ MHz}$	-	10 680	-	$\mu\text{F}$
Output capacitance	$C_{oss}$		-	1180	-	
Reverse transfer capacitance	$C_{rss}$		-	50	-	
Total gate charge <sup>c</sup>	$Q_g$	$V_{DS} = 40\text{ V}, V_{GS} = 10\text{ V}, I_D = 41.7\text{ A}$	-	151.2	227	nC
Gate-source charge <sup>c</sup>	$Q_{gs}$		-	48.4	-	
Gate-drain charge <sup>c</sup>	$Q_{gd}$		-	24	-	
Output charge	$Q_{oss}$	$V_{DS} = 40\text{ V}, V_{GS} = 0\text{ V}$	-	138	207	
Gate resistance	$R_g$	$f = 1\text{ MHz}$	0.34	1.7	3.4	$\Omega$
Turn-on delay time <sup>c</sup>	$t_{d(on)}$	$V_{DD} = 40\text{ V}, R_L = 1.2\text{ }\Omega$ $I_D \cong 33.3\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	30	60	ns
Rise time <sup>c</sup>	$t_r$		-	13	26	
Turn-off delay time <sup>c</sup>	$t_{d(off)}$		-	50	100	
Fall time <sup>c</sup>	$t_f$		-	15	30	
<b>Drain-Source Body Diode Ratings and Characteristics <sup>b</sup></b> ( $T_C = 25\text{ }^\circ\text{C}$ )						
Pulsed current ( $t = 100\text{ }\mu\text{s}$ )	$I_{SM}$		-	-	250	A
Forward voltage <sup>a</sup>	$V_{SD}$	$I_F = 10\text{ A}, V_{GS} = 0\text{ V}$	-	0.75	1.5	V
Reverse recovery time	$t_{rr}$	$I_F = 33.3\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	-	80	160	ns
Peak reverse recovery charge	$I_{RM(REC)}$		-	4	6	A
Reverse recovery charge	$Q_{rr}$		-	0.182	0.275	$\mu\text{C}$
Reverse recovery fall time	$t_a$		-	44	-	ns
Reverse recovery rise time	$t_b$		-	36	-	

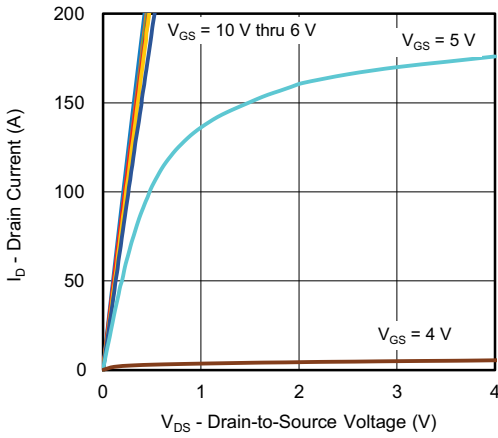
**Notes**

- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

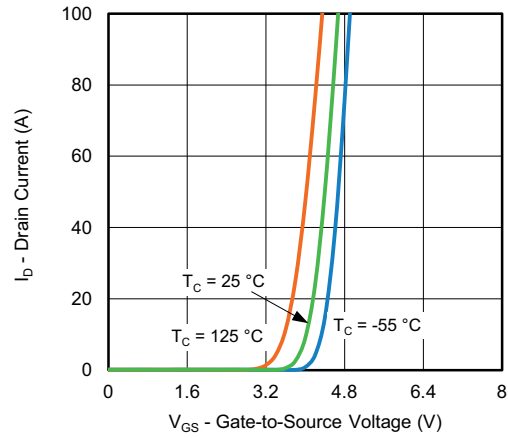
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



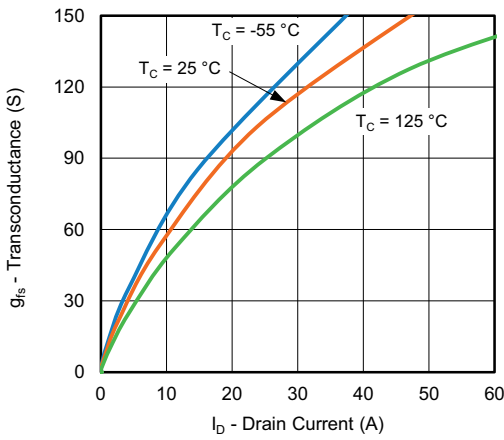
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



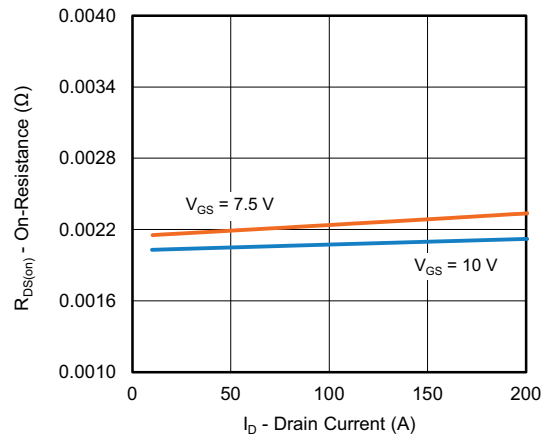
Output Characteristics



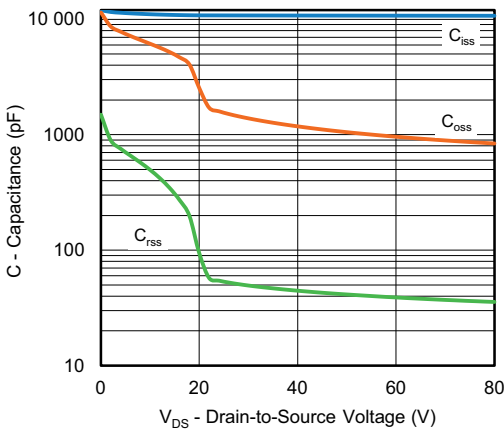
Transfer Characteristics



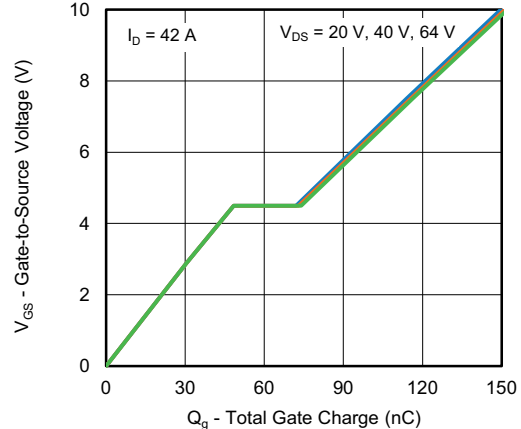
Transconductance



On-Resistance vs. Drain Current



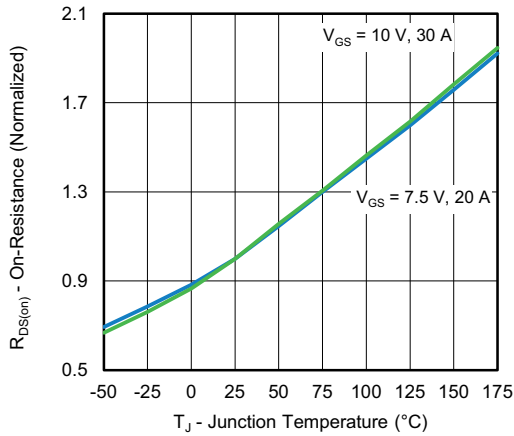
Capacitance



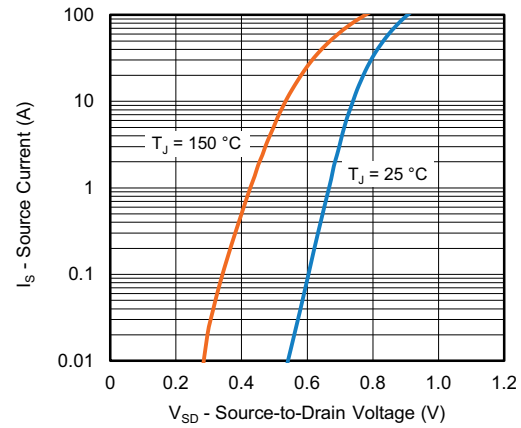
Gate Charge



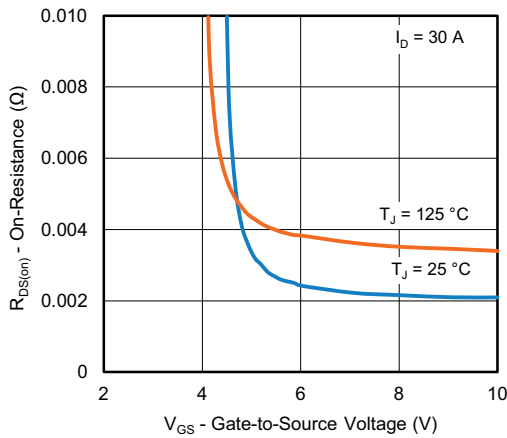
TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



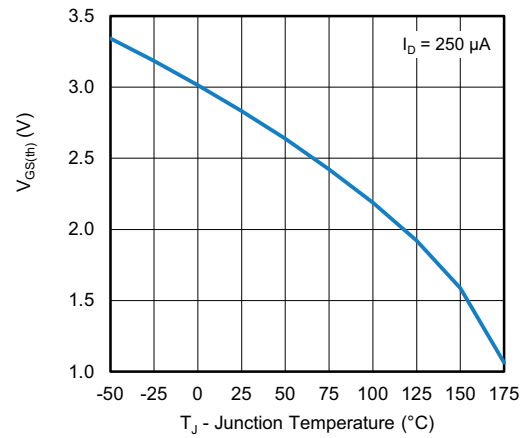
On-Resistance vs. Junction Temperature



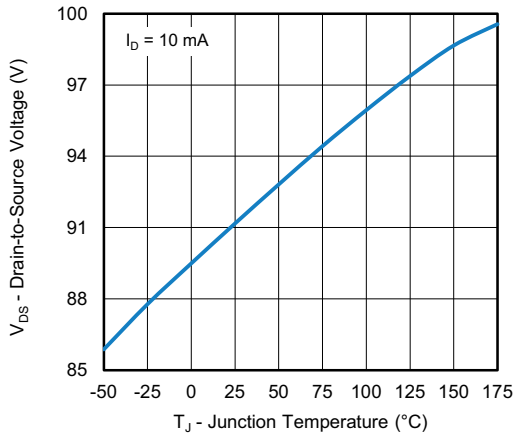
Source Drain Diode Forward Voltage



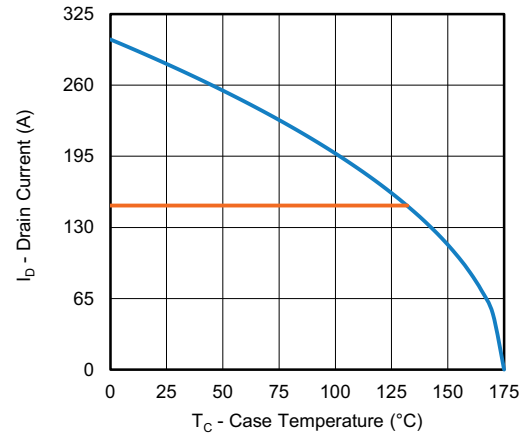
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



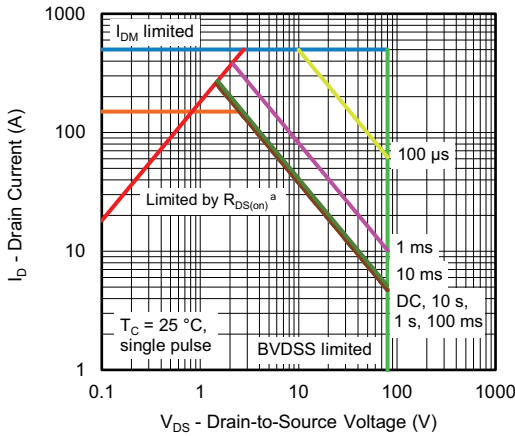
Drain Source Breakdown vs. Junction Temperature



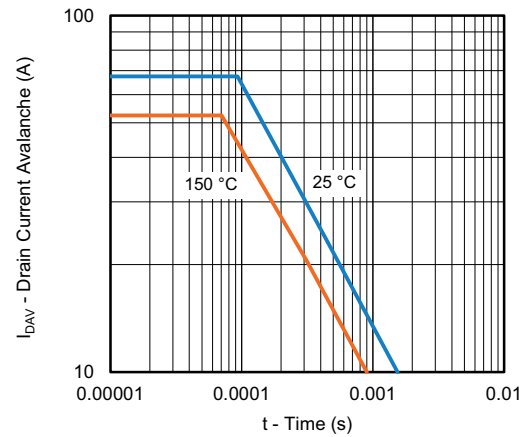
Current De-rating



**THERMAL RATINGS** ( $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted)



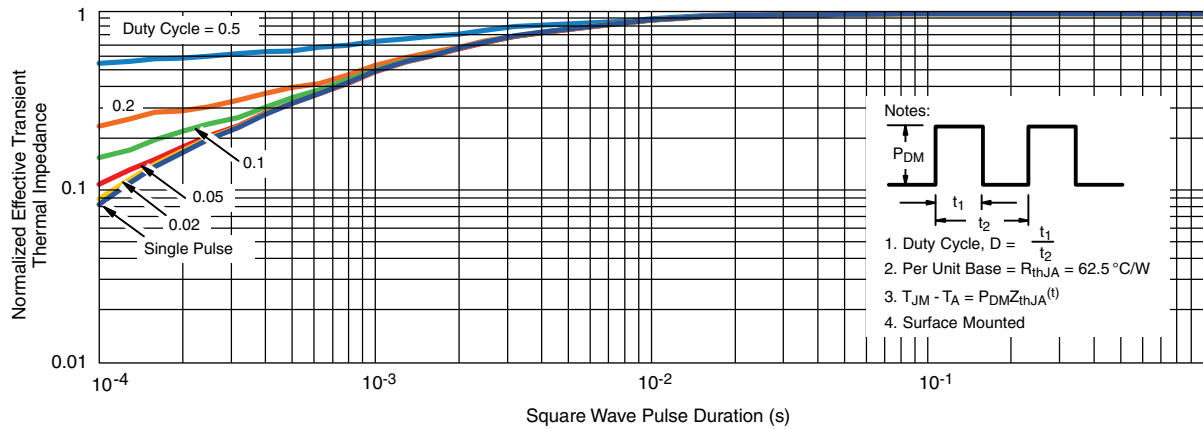
**Safe Operating Area**



**Single Pulse Avalanche Current Capability vs. Time**

**Note**

a.  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified



**Normalized Thermal Transient Impedance, Junction-to-Case**

**Note**

- The characteristics shown in the two graphs
    - Normalized Transient Thermal Impedance Junction to Ambient ( $25\text{ }^\circ\text{C}$ )
    - Normalized Transient Thermal Impedance Junction to Case ( $25\text{ }^\circ\text{C}$ )
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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